

MC74HC125A, MC74HC126A

Quad 3-State Noninverting Buffers

High-Performance Silicon-Gate CMOS

The MC74HC125A and MC74HC126A are identical in pinout to the LS125 and LS126. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

The HC125A and HC126A noninverting buffers are designed to be used with 3-state memory address drivers, clock drivers, and other bus-oriented systems. The devices have four separate output enables that are active-low (HC125A) or active-high (HC126A).

Features

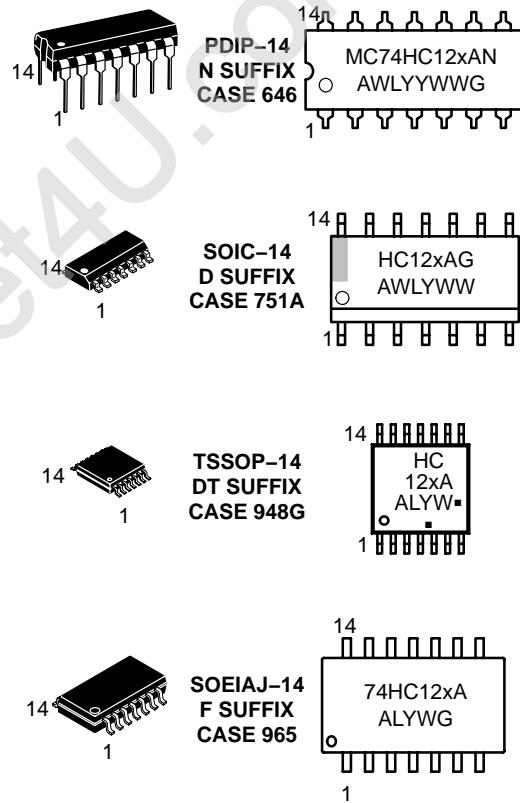
- Output Drive Capability: 15 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1.0 μ A
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the JEDEC Standard No. 7A Requirements
- Chip Complexity: 72 FETs or 18 Equivalent Gates
- Pb-Free Packages are Available*



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MARKING DIAGRAMS



A = Assembly Location
L, WL = Wafer Lot
Y, YY = Year
W, WW = Work Week
G = Pb-Free Package
▪ = Pb-Free Package
(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

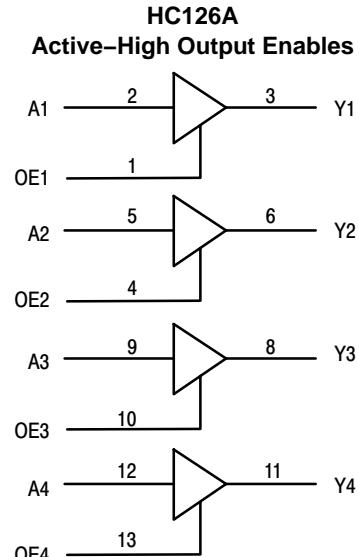
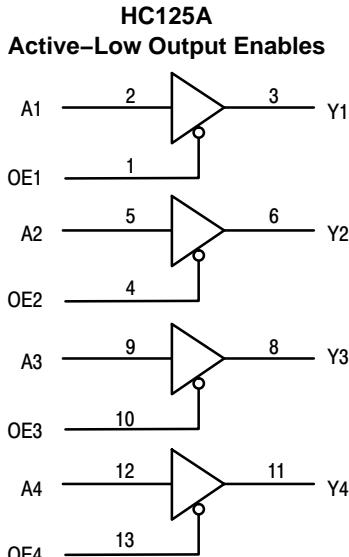
*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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PIN ASSIGNMENT

OE1	1	•	14	V _{CC}
A1	2		13	OE4
Y1	3		12	A4
OE2	4		11	Y4
A2	5		10	OE3
Y2	6		9	A3
GND	7		8	Y3

LOGIC DIAGRAM



PIN 14 = V_{CC}
PIN 7 = GND

FUNCTION TABLE

HC125A			HC126A		
Inputs	Output		Inputs	Output	
A	OE	Y	A	OE	Y
H	L	H	H	H	H
L	L	L	L	H	L
X	H	Z	X	L	Z

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)	–0.5 to +7.0	V
V _{in}	DC Input Voltage (Referenced to GND)	–0.5 to V _{CC} + 0.5	V
V _{out}	DC Output Voltage (Referenced to GND)	–0.5 to V _{CC} + 0.5	V
I _{in}	DC Input Current, per Pin	±20	mA
I _{out}	DC Output Current, per Pin	±35	mA
I _{CC}	DC Supply Current, V _{CC} and GND Pins	±75	mA
P _D	Power Dissipation in Still Air Plastic DIP† SOIC Package† TSSOP Package†	750 500 450	mW
T _{stg}	Storage Temperature	–65 to +150	°C
T _L	Lead Temperature, 1 mm from Case for 10 Seconds (Plastic DIP, SOIC or TSSOP Package)	260	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

†Derating — Plastic DIP: –10 mW/°C from 65° to 125°C

SOIC Package: –7 mW/°C from 65° to 125°C

TSSOP Package: –6.1 mW/°C from 65° to 125°C

For high frequency or heavy load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND ≤ (V_{in} or V_{out}) ≤ V_{CC}. Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)	2.0	6.0	V
V _{in} , V _{out}	DC Input Voltage, Output Voltage (Referenced to GND)	0	V _{CC}	V
T _A	Operating Temperature, All Package Types	–55	+125	°C
t _r , t _f	Input Rise and Fall Time (Figure 1)	0	1000	ns
	V _{CC} = 2.0 V	0	500	
	V _{CC} = 4.5 V	0	400	
	V _{CC} = 6.0 V	0	400	

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DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

Symbol	Parameter	Test Conditions	V _{CC} V	Guaranteed Limit			Unit
				-55 to 25°C	≤ 85°C	≤ 125°C	
V _{IH}	Minimum High-Level Input Voltage	V _{out} = V _{CC} - 0.1 V I _{out} ≤ 20 μA	2.0 3.0 4.5 6.0	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	V
V _{IL}	Maximum Low-Level Input Voltage	V _{out} = 0.1 V I _{out} ≤ 20 μA	2.0 3.0 4.5 6.0	0.5 0.9 1.35 1.8	0.5 0.9 1.35 1.8	0.5 0.9 1.35 1.8	V
V _{OH}	Minimum High-Level Output Voltage	V _{in} = V _{IH} I _{out} ≤ 20 μA	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V
		V _{in} = V _{IH} I _{out} ≤ 3.6 mA I _{out} ≤ 6.0 mA I _{out} ≤ 7.8 mA	3.0 4.5 6.0	2.48 3.98 5.48	2.34 3.84 5.34	2.2 3.7 5.2	
V _{OL}	Maximum Low-Level Output Voltage	V _{in} = V _{IL} I _{out} ≤ 20 μA	2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V
		V _{in} = V _{IL} I _{out} ≤ 3.6 mA I _{out} ≤ 6.0 mA I _{out} ≤ 7.8 mA	3.0 4.5 6.0	0.26 0.26 0.26	0.33 0.33 0.33	0.4 0.4 0.4	
I _{in}	Maximum Input Leakage Current	V _{in} = V _{CC} or GND	6.0	± 0.1	± 1.0	± 1.0	μA
I _{OZ}	Maximum Three-State Leakage Current	Output in High-Impedance State V _{in} = V _{IL} or V _{IH} V _{out} = V _{CC} or GND	6.0	± 0.5	± 5.0	± 10	μA
I _{CC}	Maximum Quiescent Supply Current (per Package)	V _{in} = V _{CC} or GND I _{out} = 0 μA	6.0	4.0	40	160	μA

NOTE: Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

AC ELECTRICAL CHARACTERISTICS (C_L = 50 pF, Input t_r = t_f = 6.0 ns)

Symbol	Parameter	V _{CC} V	Guaranteed Limit			Unit
			-55 to 25°C	≤ 85°C	≤ 125°C	
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Input A to Output Y (Figures 1 and 3)	2.0 3.0 4.5 6.0	90 36 18 15	115 45 23 20	135 60 27 23	ns
t _{PLZ} , t _{PHZ}	Maximum Propagation Delay, Output Enable to Y (Figures 2 and 4)	2.0 3.0 4.5 6.0	120 45 24 20	150 60 30 26	180 80 36 31	ns
t _{PZL} , t _{PZH}	Maximum Propagation Delay, Output Enable to Y (Figures 2 and 4)	2.0 3.0 4.5 6.0	90 36 18 15	115 45 23 20	135 60 27 23	ns
t _{TLH} , t _{THL}	Maximum Output Transition Time, Any Output (Figures 1 and 3)	2.0 3.0 4.5 6.0	60 22 12 10	75 28 15 13	90 34 18 15	ns
C _{in}	Maximum Input Capacitance	—	10	10	10	pF
C _{out}	Maximum 3-State Output Capacitance (Output in High-Impedance State)	—	15	15	15	pF

NOTE: For propagation delays with loads other than 50 pF, and information on typical parametric values, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

C _{PD}	Power Dissipation Capacitance (Per Buffer)*	Typical @ 25°C, V _{CC} = 5.0 V		pF
		30	30	

* Used to determine the no-load dynamic power consumption: P_D = C_{PD} V_{CC}²f + I_{CC} V_{CC}. For load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

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ORDERING INFORMATION

Device	Package	Shipping [†]
MC74HC125AN	PDIP-14	500 Units / Rail
MC74HC125ANG	PDIP-14 (Pb-Free)	500 Units / Rail
MC74HC125AD	SOIC-14	55 Units / Rail
MC74HC125ADG	SOIC-14 (Pb-Free)	55 Units / Rail
MC74HC125ADR2	SOIC-14	2500 Units / Reel
MC74HC125ADR2G	SOIC-14 (Pb-Free)	2500 Units / Reel
MC74HC125ADT	TSSOP-14*	96 Units / Rail
MC74HC125ADTG	TSSOP-14*	96 Units / Rail
MC74HC125ADTR2	TSSOP-14*	2500 Units / Reel
MC74HC125ADTR2G	TSSOP-14*	2500 Units / Reel
MC74HC125AF	SOEIAJ-14	50 Units / Rail
MC74HC125AFG	SOEIAJ-14 (Pb-Free)	50 Units / Rail
MC74HC125AFEL	SOEIAJ-14	2000 Units / Reel
MC74HC125AFELG	SOEIAJ-14 (Pb-Free)	2000 Units / Reel
MC74HC126AN	PDIP-14	500 Units / Rail
MC74HC126ANG	PDIP-14 (Pb-Free)	500 Units / Rail
MC74HC126AD	SOIC-14	55 Units / Rail
MC74HC126ADG	SOIC-14 (Pb-Free)	55 Units / Rail
MC74HC126ADR2	SOIC-14	2500 Units / Reel
MC74HC126ADR2G	SOIC-14 (Pb-Free)	2500 Units / Reel
MC74HC126ADTR2	TSSOP-14*	2500 Units / Reel
MC74HC126ADTR2G	TSSOP-14*	2500 Units / Reel
MC74HC126AFEL	SOEIAJ-14	2000 Units / Reel
MC74HC126AFELG	SOEIAJ-14 (Pb-Free)	2000 Units / Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*This package is inherently Pb-Free.

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SWITCHING WAVEFORMS

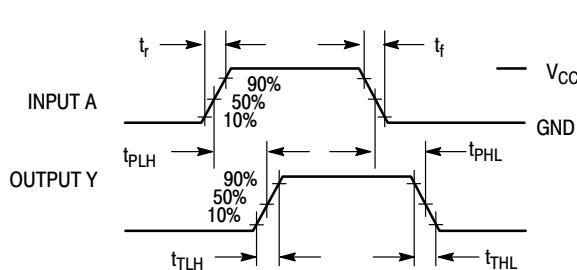


Figure 1.

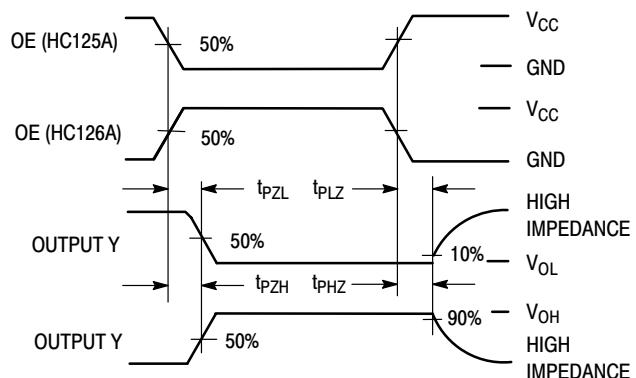
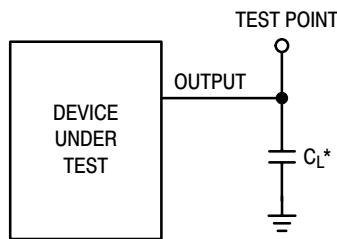
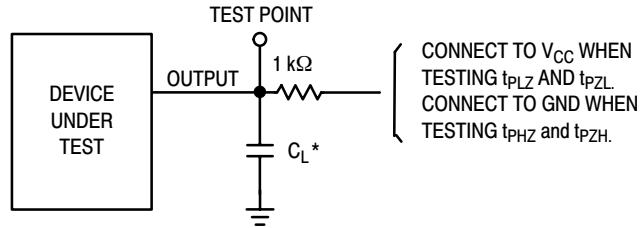


Figure 2.



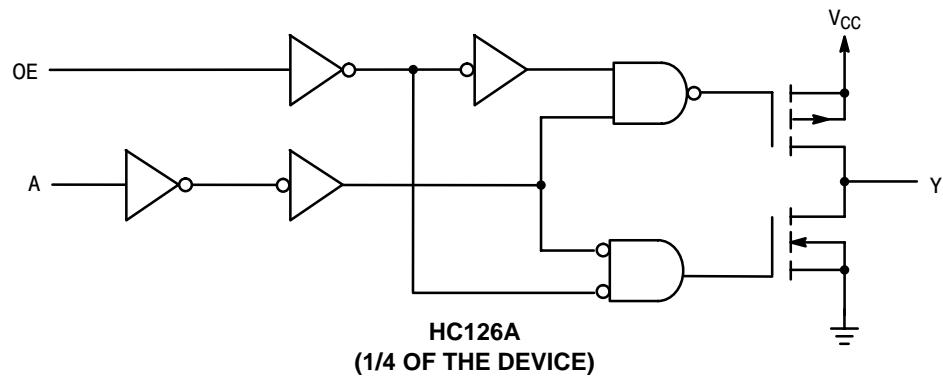
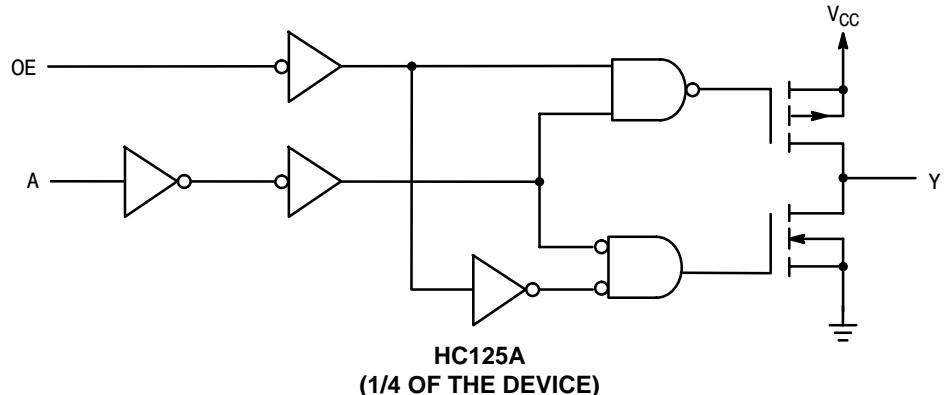
*Includes all probe and jig capacitance

Figure 3. Test Circuit



*Includes all probe and jig capacitance

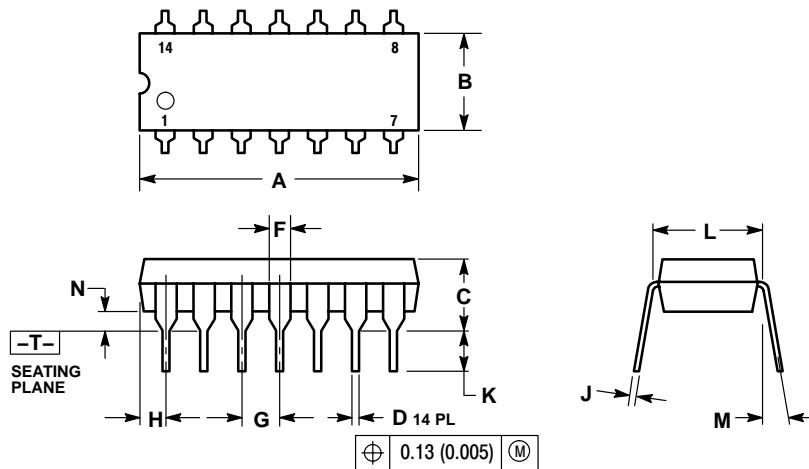
Figure 4. Test Circuit



MC74HC125A, MC74HC126A

PACKAGE DIMENSIONS

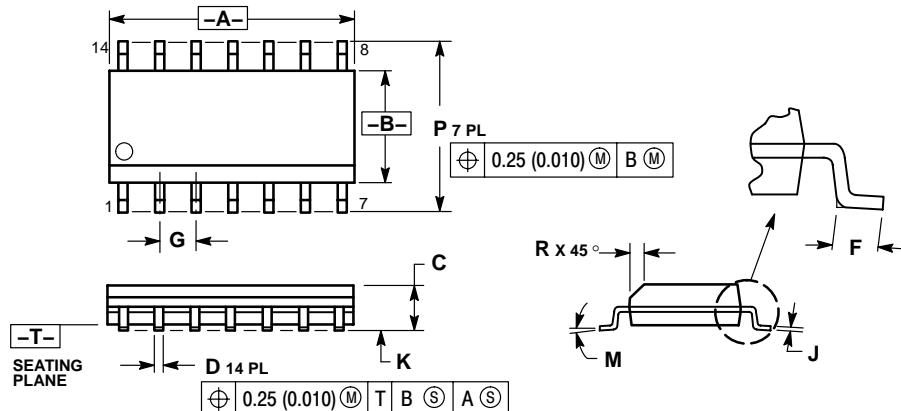
**PDIP-14
N SUFFIX
CASE 646-06
ISSUE N**



NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
 4. DIMENSION B DOES NOT INCLUDE MOLD FLASH.
 5. ROUNDED CORNERS OPTIONAL.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.715	0.770	18.16	18.80
B	0.240	0.260	6.10	6.60
C	0.145	0.185	3.69	4.69
D	0.015	0.021	0.38	0.53
F	0.040	0.070	1.02	1.78
G	0.100 BSC		2.54 BSC	
H	0.052	0.095	1.32	2.41
J	0.008	0.015	0.20	0.38
K	0.115	0.135	2.92	3.43
L	0.290	0.310	7.37	7.87
M	—	10°	—	10°
N	0.015	0.039	0.38	1.01

**SOIC-14
D SUFFIX
CASE 751A-03
ISSUE G**



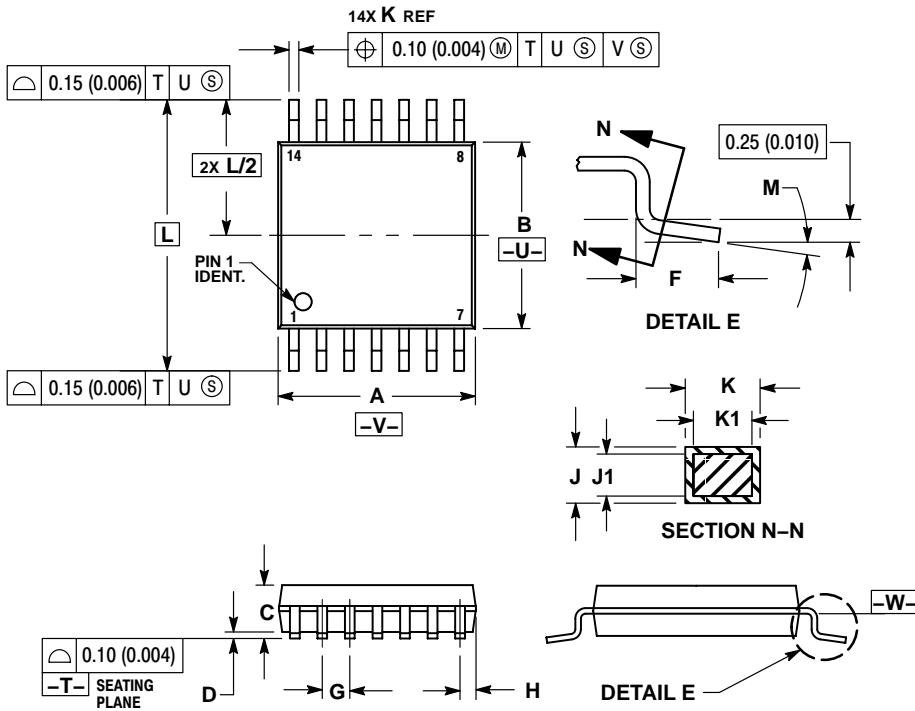
NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
 5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	8.55	8.75	0.337	0.344
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050 BSC	
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
P	5.80	6.20	0.228	0.244
R	0.25	0.50	0.010	0.019

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PACKAGE DIMENSIONS

**TSSOP-14
DT SUFFIX
CASE 948G-01
ISSUE A**



NOTES:

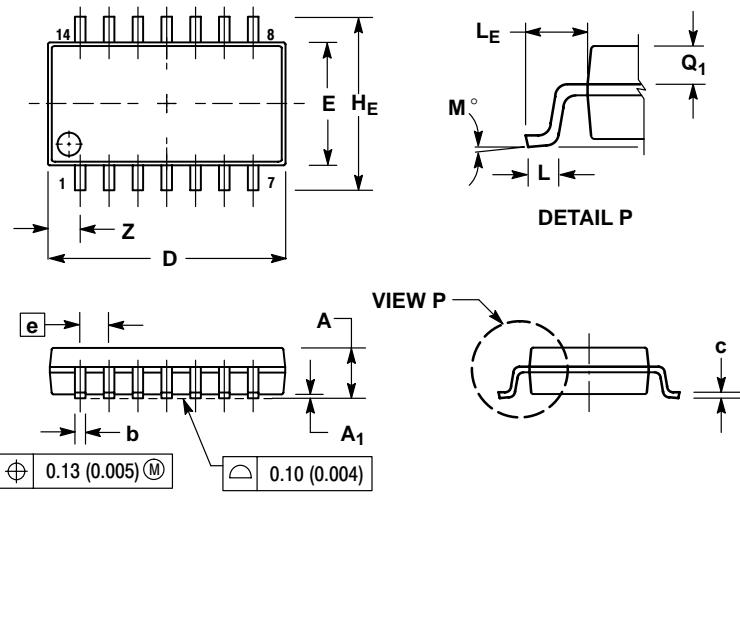
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.90	5.10	0.193	0.200
B	4.30	4.50	0.169	0.177
C	----	1.20	----	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
H	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0°	8°	0°	8°

MC74HC125A, MC74HC126A

PACKAGE DIMENSIONS

SOEIAJ-14
F SUFFIX
CASE 965-01
ISSUE O



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
5. THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	---	2.05	---	0.081
A ₁	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
c	0.18	0.27	0.007	0.011
D	9.90	10.50	0.390	0.413
E	5.10	5.45	0.201	0.215
e	1.27 BSC		0.050 BSC	
H _E	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
L _E	1.10	1.50	0.043	0.059
M	0°	10°	0°	10°
Q ₁	0.70	0.90	0.028	0.035
Z	---	1.42	---	0.056

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